

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_{D \max}$ $T_A = +25^\circ\text{C}$
P-Channel	-12V	61mΩ @ $V_{GS} = -4.5\text{V}$	-3.8A
		81mΩ @ $V_{GS} = -2.5\text{V}$	-3.3A
		115mΩ @ $V_{GS} = -1.8\text{V}$	-2.8A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

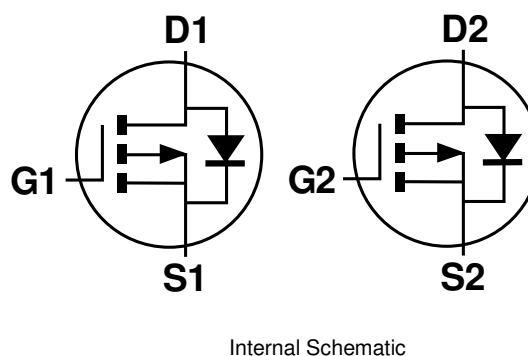
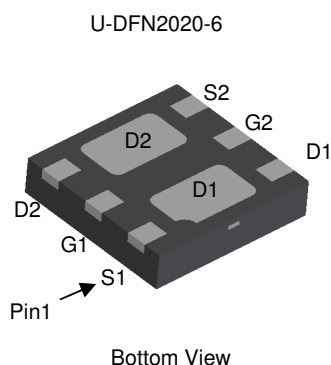
- Load Switch
- Power Management Functions
- Portable Power Adaptors

Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(e4)
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

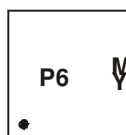

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1046UFDB -7	U-DFN2020-6	3,000/Tape & Reel
DMP1046UFDB -13	U-DFN2020-6	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information

U-DFN2020-6



P6 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.8 -3.0	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	-5.0 -4.0	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-1	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	-15	A
Avalanche Current (L = 0.1mH)			I _{AS}	-12	A
Avalanche Energy (L = 0.1mH)			E _{AS}	8	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P _D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	92	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	20	°C
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	

Notes: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-	-1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	37	61	mΩ	V _{GS} = -4.5V, I _D = -3.6A
		-	47	81		V _{GS} = -2.5V, I _D = -3.2A
		-	63	115		V _{GS} = -1.8V, I _D = -1.0A
		-	-	-		V _{GS} = -1.8V, I _D = -1.0A
Diode Forward Voltage	V _{SD}	-	-0.65	-1.2	V	V _{GS} = 0V, I _S = -4.5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	915	-	pF	V _{DS} = -6V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	225	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	183	-	pF	
Gate Resistance	R _g	-	56.9	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	-	10.7	-	nC	V _{DS} = -6V, I _D = -4.3A
Total Gate Charge (V _{GS} = -8V)		-	17.9	-	nC	
Gate-Source Charge	Q _{gs}	-	1.7	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.0	-	nC	
Turn-On Delay Time	t _{D(on)}	-	5.7	-	ns	V _{DD} = -6V, V _{GS} = -4.5V, R _L = 1.6Ω, R _G = 1Ω
Turn-On Rise Time	t _r	-	11.5	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	27.8	-	ns	
Turn-Off Fall Time	t _f	-	26.4	-	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

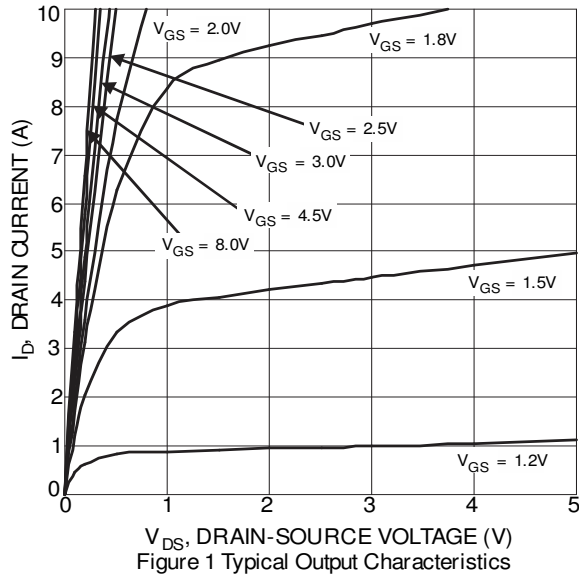


Figure 1 Typical Output Characteristics

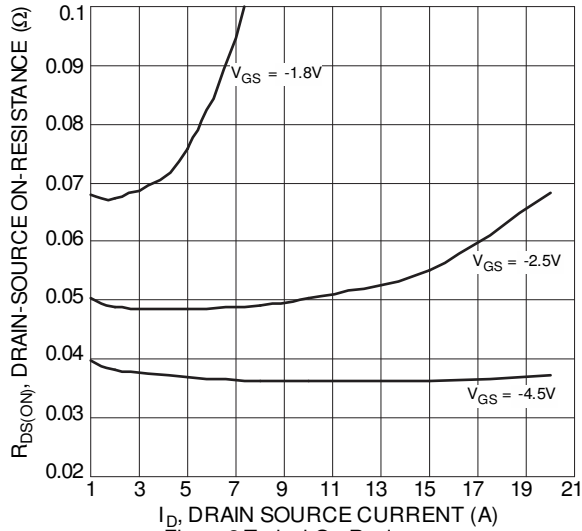


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

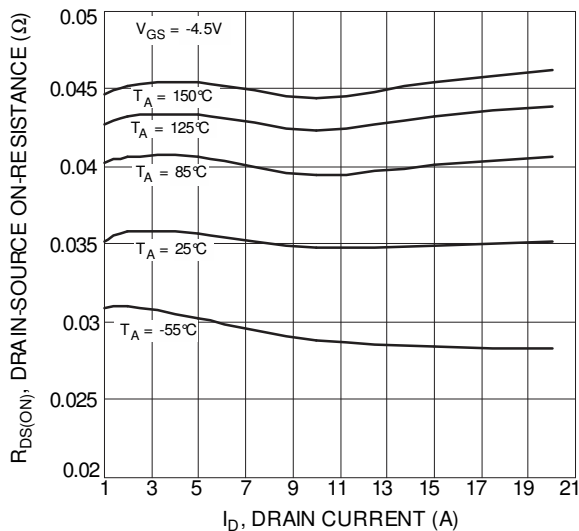


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

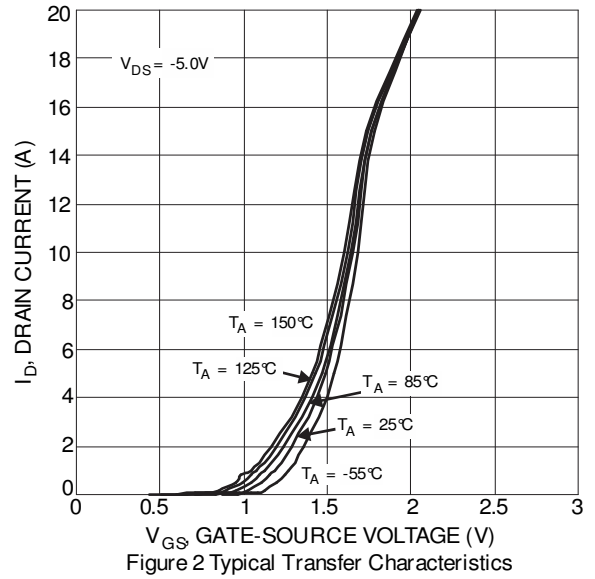


Figure 2 Typical Transfer Characteristics

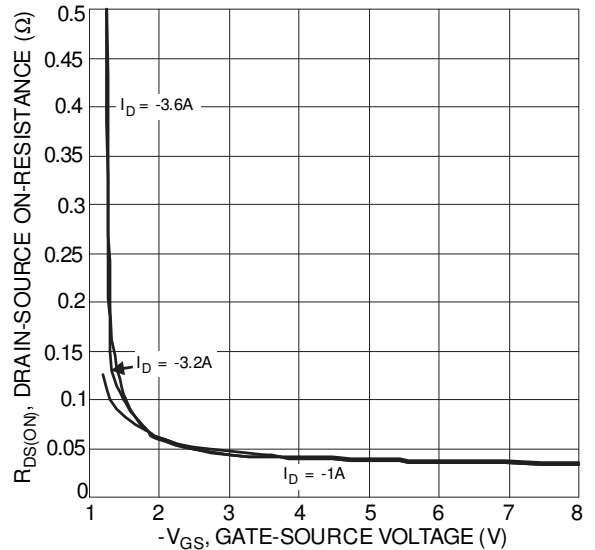


Figure 4 Typical Transfer Characteristics

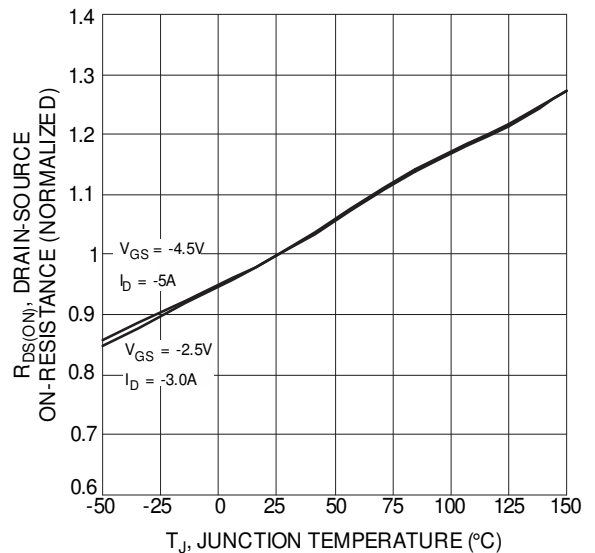
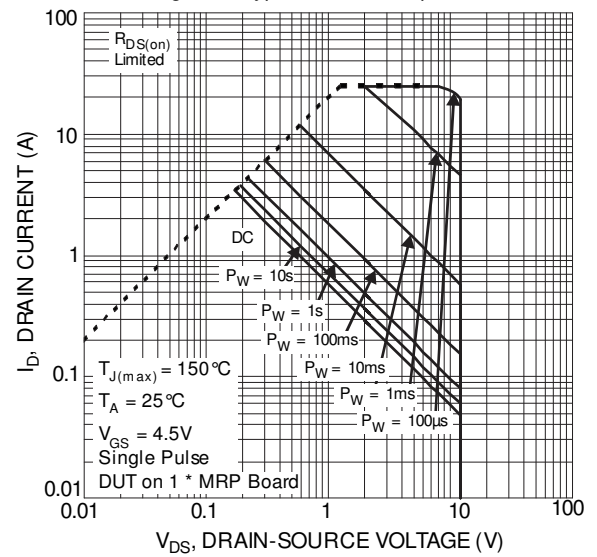
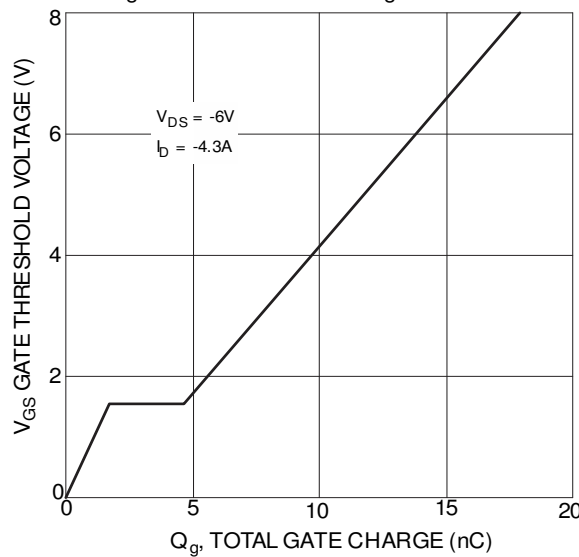
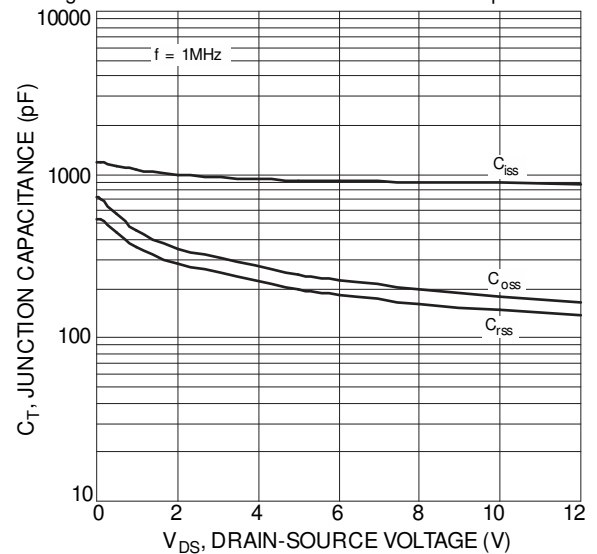
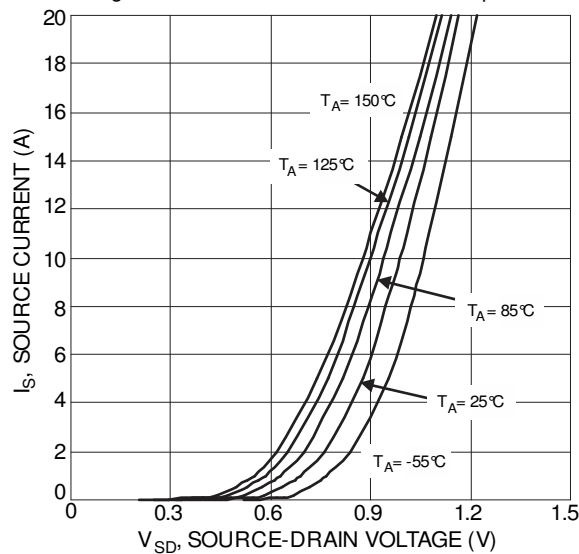
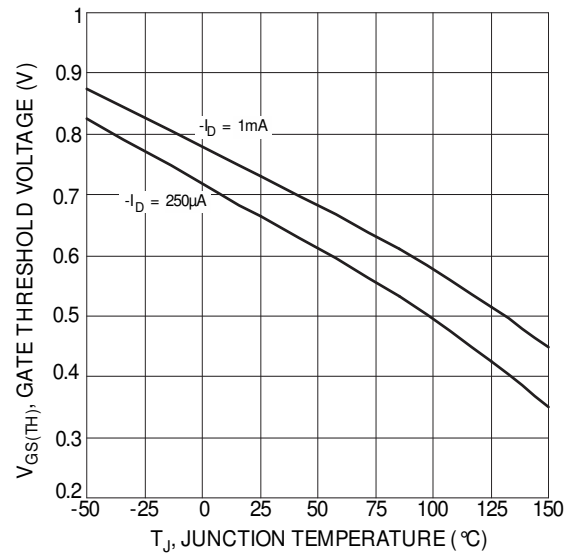
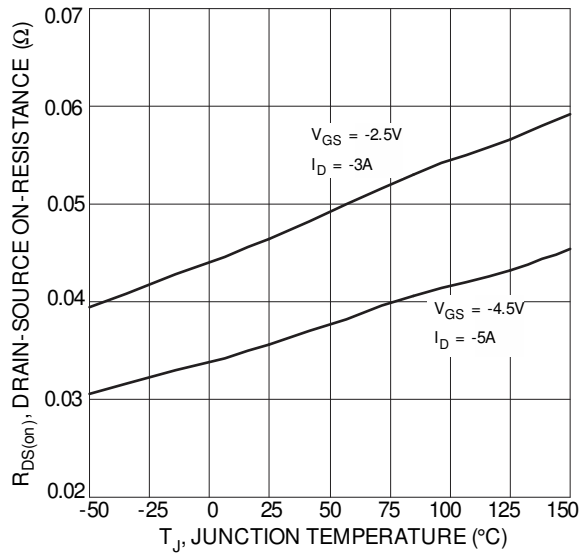
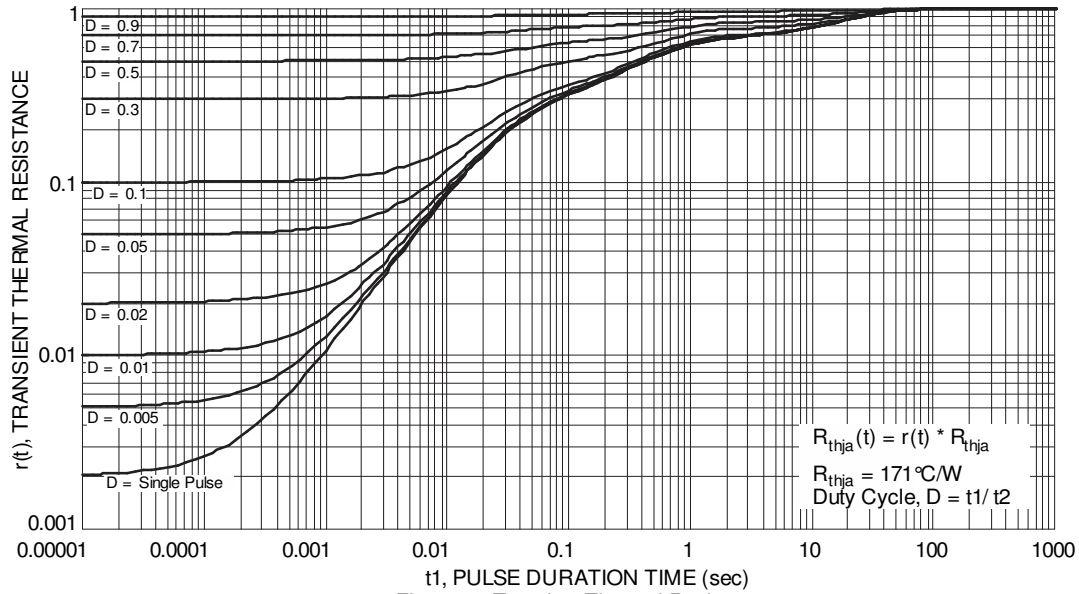


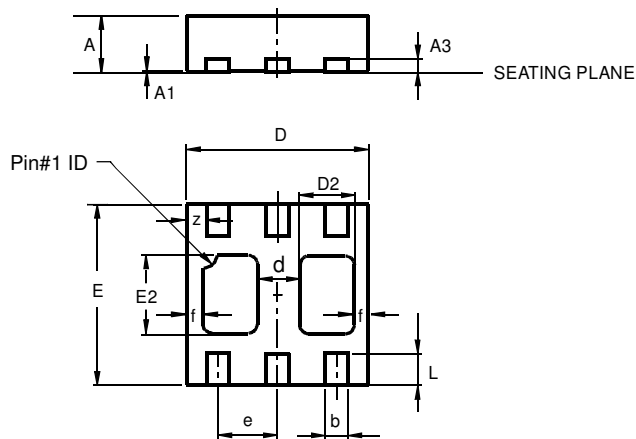
Figure 6 On-Resistance Variation with Temperature





Package Outline Dimensions

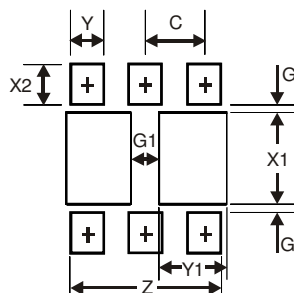
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
d	—	—	0.45
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
f	—	—	0.15
L	0.25	0.35	0.30
z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
C	0.65

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